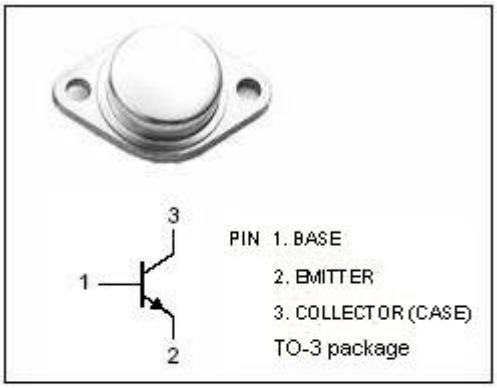
isc Silicon NPN Power Transistor — 2SD310

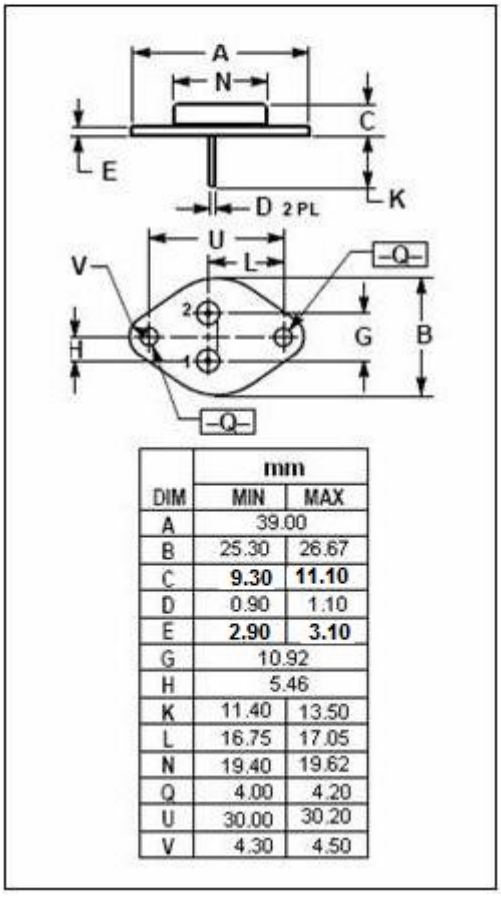
DESCRIPTION

- High Collector-Emitter Sustaining Voltage-
  : $V_{CEO(SUS)}$= 400V (Min)
- High Switching Speed
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



APPLICATIONS

- Power switching
- Power amplification
- Power driver



DIM	mm MIN	MAX
A	39.00	
B	25.30	26.67
C	**9.30**	**11.10**
D	0.90	1.10
E	**2.90**	**3.10**
G	10.92	
H	5.46	
K	11.40	13.50
L	16.75	17.05
N	19.40	19.62
Q	4.00	4.20
U	30.00	30.20
V	4.30	4.50

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	MAX	UNIT
V_{CBO}	Collector-Base Voltage	800	V
V_{CEO}	Collector-Emitter Voltage	400	V
V_{EBO}	Emitter-Base Voltage	10	V
I_C	Collector Current-Continuous	15	A
I_B	Base Current-Continuous	6	A
P_C	Collector Power Dissipation @T_C=25℃	150	W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-65~150	℃

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C= 50mA;Ib=0	400			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 6A; I_B= 1.2A			1.2	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= 6A; I_B= 1.2A			1.5	V
h_{FE-1}	DC Current Gain	I_C= 1A ; V_{CE}= 5V	15		50	
h_{FE-2}	DC Current Gain	I_C=7.5A; V_{CE}= 5V	10			
I_{CBO}	Collector Cutoff Current	V_{CB}= 800V; I_E= 0			0.1	mA
I_{CEO}	Collector Cutoff Current	V_{CE}= 400V; I_B= 0			0.5	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 5V; I_C= 0			0.1	mA